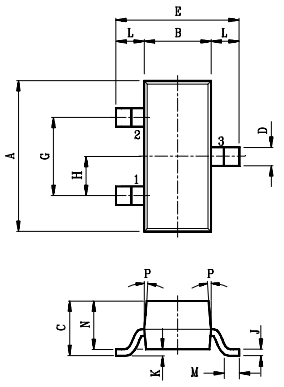
BSS63

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-110	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-100	mA
Emitter Current	I_E	100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-65~150	℃

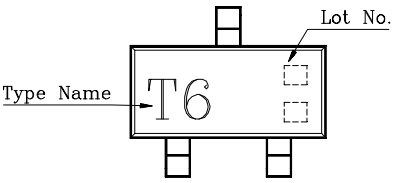


DIM	MILLIMETERS
A	2.93±0.20
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.45+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
H	0.95
J	0.13+0.10/-0.05
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10
P	7°

1. EMITTER
2. BASE
3. COLLECTOR

SOT-23

Marking



ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-100	-	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-10μA, I_E=0	-110	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-6	-	-	V
Collector Cut-off Current	I_{CBO}	V_{CB}=-90V, I_E=0	-	-	-100	nA
		V_{CB}=-90V, I_E=0, Ta=150℃	-	-	-50	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-200	nA
DC Current Gain	h_{FE}	V_{CE}=-1V, I_C=-10mA	30	-	-	
		V_{CE}=-1V, I_C=-25mA	30	-	-	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-25mA, I_B=-2.5mA	-	-	-0.9	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-25mA, I_B=-2.5mA	-	-	-0.25	V
		I_C=-75mA, I_B=-7.5mA	-	-	-0.9	
Transition Frequency	f_T	I_C=-25mA, V_{CE}=-5V, f=100MHz	50	-	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	3	-	pF